

SYSTEM AND METHOD FOR READING A MEMORY CELL

Abstract of the Disclosure

A method of performing a read operation from a first magnetic random access memory (MRAM) cell in a memory cell string that includes the first MRAM cell coupled to a second MRAM cell. The method includes providing a voltage to a first end of the first memory cell string that is closest to the first MRAM cell, providing a ground source to a second end of the first memory cell string that is opposite the first end, and determining whether a voltage change occurred at a node between the first and second MRAM cells in response to applying a write sense current to the first MRAM cell.